

Towards optimization of the Josephson diode effect

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We theoretically study the Josephson diode effect in the junction of singlet superconductors separated by the Rashba system in the in-plane magnetic field perpendicular to the applied current. The coupling energy of two superconductors is analytically calculated using a tunneling Hamiltonian with a one-dimensional model. It is found that the critical current is asymmetric with respect to the current and the magnetic field, i.e., Josephson diode effect. Depending on a distance between the superconducting electrodes d , the Josephson diode effect changes its magnitude and sign. The magnitude is inversely proportional to a band split caused by the spin-orbit interaction. Since d is experimentally controllable, the Josephson diode effect can be optimized by tuning of d . Our theory develops a new guiding principle to design the Josephson diode device.

I. INTRODUCTION

The superconducting diode effect is a phenomenon whereby the superconducting critical current (I_c) depends on the direction of an applied current in a magnetic field. The asymmetry of I_c has been observed in a metal-semiconductor multilayer and is associated with an asymmetric flux flow [1, 2]. The superconducting diode effect has also been reported using a high- T_c cuprate/ferromagnetic manganese heterostructure for magnetic memory applications [3]. Recently, Ando et al. have reported the superconducting diode effect in the multilayer composed of three elements, i.e., Nb, Ta, and V without an inversion center [4, 5]. They have reported that their superconducting diode effect arises from the magnetochiral anisotropy effect induced by a spin-orbit interaction. This is different from the flux flow mechanism and has inspired many studies of the superconducting diode effect [6–8]. The theoretical studies propose that the superconducting diode effect is caused by the spatial variation of the superconducting order parameter, e.g., helical superconductor, due to the spin-orbit interaction [9–13].

Motivated by the superconducting diode effect, the non-reciprocity of I_c in Josephson junctions is also studied experimentally [14–19]. A typical device consists of two superconducting electrodes coupled via a two dimensional electron system with a spin-orbit interaction, i.e., Rashba system [20, 21]. The current-voltage curve of Josephson junction is measured by applying a current I_B . When the in-plane magnetic field perpendicular to I_B is simultaneously applied to the Rashba system (See Fig. 1 (a)), I_c with positive current (I_c^+) is different from I_c with negative current (I_c^-), i.e., $I_c^+ \neq I_c^-$ (See Fig. 1 (b)). The phenomenon is reversed by reversing the direction of the magnetic field. We call it Josephson diode effect instead of the superconducting diode effect.

Theoretically, the Josephson junction via the Rashba system with a magnetic field was studied by Bezuglyi et al. [22], although the Josephson diode effect was not addressed. They reported I_c oscillates with the magnetic field or the distance of superconducting electrodes, d . This is the same mechanism as the superconductor/ferromagnet/superconductor (SFS) junction [23, 24], in which I_c changes its sign with d [25–34]. The negative I_c means that the current-phase relation shifted by π , i.e., the π -junction [23, 24]. It is expected to provide various applications for classical digital logic elements and flux-bias-free flux qubit [35, 36]. The distance between superconductors essentially changes the transport property of Josephson junction and opens a new pathway for the application. Regarding the Josephson diode effect, on the other hand, recent theoretical studies have not addressed such d -dependence so far [37–42]. Buzdin proposed the φ -junction, in which the superconducting order parameter in the Rashba system is spatially modulated due to the spin-orbit interaction and the magnetic field [37]. The spatial modulation makes the current-phase relation shifted by an intermediate value between 0 and π . Yokoyama et al., numerically examined the φ -junction and reported the directional dependence of the critical current [38]. The Andreev bound state is examined to calculate the current phase relation of a short junction with a transparent interface [40–42]. However, the spatial variation of the Josephson diode effect has not been taken into account.

In this paper, we study the Josephson diode effect in the junction of two singlet superconductors separated by the Rashba system with distance d . The coupling energy of two superconductors is analytically calculated using a tunneling Hamiltonian with a one-dimensional model. We find that the magnitude and the sign of $I_c^+ - I_c^-$ depends on d . This paper is organized as follows: Sec. II presents the model and Hamiltonian; Sec. III provides a coupling energy of the junction in the fourth order of tunneling matrix element; Sec. IV, the Josephson diode effect is examined by calculating the coupling energy with the applied current. We show the d -dependence of the

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Josephson diode effect. Sec. V provides a summary. The reduced Planck constant \hbar and the Boltzmann constant k_B are taken to be unity.

II. HAMILTONIAN: LINEARIZED ONE-DIMENSIONAL MODEL

The Josephson junction separated by the Rashba system is illustrated in Fig. 1 (a). Under the in-plane magnetic field h_y perpendicular to I_B , I_c in the positive branch I_c^+ (red) is different from I_c in the negative branch I_c^- (blue) as shown in Fig. 1 (b). The difference between I_c^+ and I_c^- , i.e., $I_c^+ - I_c^-$, is reversed by reversing I_B or h_y . Therefore, the Josephson diode effect is characterized by $I_c^+ - I_c^- \propto I_B \cdot h_y$ [43]. I_c of Josephson junction is calculated using the Josephson coupling energy between two superconductors (SCs). The current-phase relation is also derived by taking the derivative of the coupling energy with respect to the phase difference of two SCs. In order to obtain an analytical formula of the coupling energy, we use a one-dimensional model, in which the dispersion relation of electrons is linearized around the Fermi momentum $\pm k_F$.

The Hamiltonian of singlet SC in left (SC_L, $\lambda = L$) and right (SC_R, $\lambda = R$) electrode is given by,

$$H_\lambda = \sum_{k,\sigma=\pm} \left[v_F (k - k_F) a_{\lambda k \sigma}^\dagger a_{\lambda k \sigma} - v_F (k + k_F) b_{\lambda k \sigma}^\dagger b_{\lambda k \sigma} \right] \\ + \sum_{k,\sigma=\pm} \left[v_F (k + k_F) a_{\lambda \bar{k} \sigma}^\dagger a_{\lambda \bar{k} \sigma} - v_F (k - k_F) b_{\lambda \bar{k} \sigma}^\dagger b_{\lambda \bar{k} \sigma} \right] \\ + \sum_{k,\sigma=\pm} \left[\sigma \Delta \left(a_{\lambda k \sigma}^\dagger b_{\lambda \bar{k} \bar{\sigma}}^\dagger + b_{\lambda k \sigma}^\dagger a_{\lambda \bar{k} \bar{\sigma}}^\dagger \right) \right. \\ \left. - \sigma \Delta^* \left(b_{\lambda \bar{k} \bar{\sigma}} a_{\lambda k \sigma} + a_{\lambda \bar{k} \bar{\sigma}} b_{\lambda k \sigma} \right) \right], \quad (1)$$

$$\Delta \equiv \mathcal{I} \langle a_{\lambda k} b_{\lambda \bar{k}} - a_{\lambda k} b_{\lambda \bar{k}} \rangle, \quad (2)$$

with momentum k ($\bar{k} \equiv -k$), Fermi velocity v_F , and electrons spin σ ($\bar{\sigma} \equiv -\sigma$). The singlet superconducting state by interaction \mathcal{I} is assumed in the both electrodes. The electron creation (annihilation) operators around $+k_F$ and $-k_F$ are denoted by $a_{\lambda k \sigma}^\dagger$ and $b_{\lambda k \sigma}^\dagger$ ($a_{\lambda k \sigma}$ and $b_{\lambda k \sigma}$), respectively.

In our theory, the Rashba system is introduced by the following one-dimensional model,

$$H_M = H_1 + H_2 + H_3 + H_4 \quad (3)$$

$$H_1 = \sum_{k,\sigma,\sigma'} a_{k\sigma}^\dagger \{ [v_F (k - k_F) - \gamma h_z \tau_{3\sigma\sigma'}] - (\alpha_R k_F - \gamma h_y) \tau_{2\sigma\sigma'} \} a_{k\sigma} \quad (4)$$

$$H_2 = \sum_{k,\sigma,\sigma'} b_{k\sigma}^\dagger \{ [-v_F (k + k_F) - \gamma h_z \tau_{3\sigma\sigma'}] + (\alpha_R k_F + \gamma h_y) \tau_{2\sigma\sigma'} \} b_{k\sigma} \quad (5)$$

$$H_3 = \sum_{k,\sigma,\sigma'} a_{\bar{k}\sigma}^\dagger \{ [v_F (k + k_F) + \gamma h_z \tau_{3\sigma\sigma'}] + (\alpha_R k_F - \gamma h_y) \tau_{2\sigma\sigma'} \} a_{\bar{k}\sigma}^\dagger \quad (6)$$

$$H_4 = \sum_{k,\sigma,\sigma'} b_{\bar{k}\sigma}^\dagger \{ [-v_F (k - k_F) + \gamma h_z \tau_{3\sigma\sigma'}] - (\alpha_R k_F + \gamma h_y) \tau_{2\sigma\sigma'} \} b_{\bar{k}\sigma}^\dagger, \quad (7)$$

with the Pauli matrix τ_n ($n = 1, 2, 3$), external magnetic field in y (z) direction h_y (h_z), and a Rashba parameter α_R [20, 21]. The parameter γ is defined by $\gamma \equiv g\mu_B$ with electron g -factor g and Bohr magneton μ_B . The electron creation (annihilation) operators around $+k_F$ and $-k_F$ are denoted by $a_{k\sigma}^\dagger$ and $b_{k\sigma}^\dagger$ ($a_{k\sigma}$ and $b_{k\sigma}$), respectively. A spin configuration on each Fermi point $\pm k_F$ depends on a momentum due to the spin-orbit interaction as shown in Fig. 2, in which the solid lines shows the dispersion relation on the right and left going electrons E_R and E_L given by,

$$E_R = v_F (k - k_F) \pm |\alpha_R k_F - \gamma h_y|, \quad (8)$$

$$E_L = -v_F (k + k_F) \pm |\alpha_R k_F + \gamma h_y|. \quad (9)$$

The circles with blue dot and red cross indicate spin direction parallel and anti-parallel to the y -direction on

each Fermi point, respectively. In the right branch, the blue (red) lines corresponds to the positive (negative) sign of Eq. (8), and in the left branch vice versa with Eq. (9). The dotted broken line shows the dispersion relations without α_R nor h_y . The dotted line is split into a couple of blue and red solid lines by α_R . The splitting of two bands is given by $2\alpha_R k_F$ for $h_y = 0$ (upper panel of Fig. 2). Increasing h_y , the splittings of the left and right branches become no longer the same as, $2|\alpha_R k_F + \gamma h_y|$ for the left, and $2|\alpha_R k_F - \gamma h_y|$ for the right. In the right branch, the two bands with red and blue merge into one at $h_y = \alpha_R k_F / \gamma \equiv h_c$ and split again swapping the spin orientation. It should be noted that physical property will not have singularity around h_c .

The tunneling Hamiltonian H_{TL} (H_{TR}) between SC_L

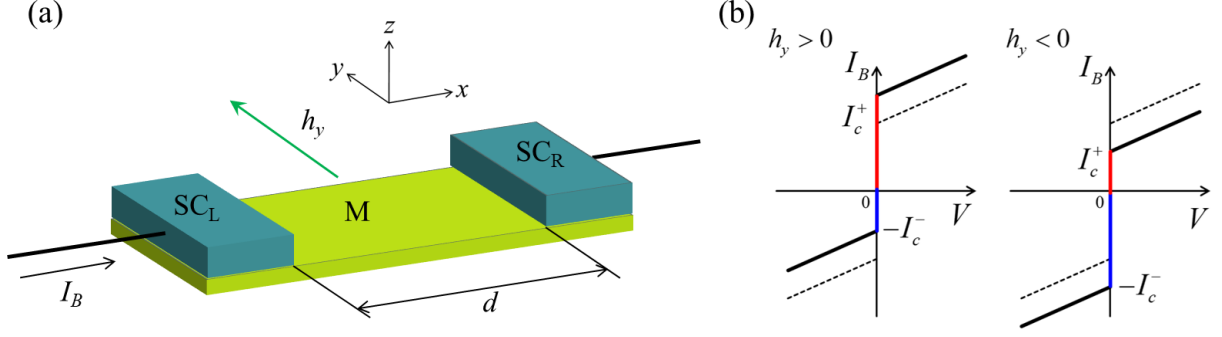


FIG. 1. (a) The device geometry of the Josephson junction through the Rashba system (M). The two SCs (SC_R and SC_L) are separated by the Rashba system with distance d . An external magnetic field h_y is applied in the direction perpendicular to the applied current I_B . The signs of I_B and h_y are defined by the Cartesian coordinate shown in this panel. (b) The schematics of the current-voltage curve of the Josephson junction. Due to the Josephson diode effect, I_c in the positive branch (I_c^+) colored by red is different from that in the negative one (I_c^-) colored by blue. The broken line is the curve without magnetic field, i.e., $h_y = 0$. For $h_y > 0$ ($h_y < 0$), the curve is shifted up (down) from that with $h_y = 0$. The amount of the shift is reversed by reversing h_y . The Josephson diode effect is characterized by $I_c^+ - I_c^- \propto I_B \cdot h_y$

$$E_L = -v_F(k + k_F) \pm |\alpha_R k_F + \gamma h_y| \quad E_R = v_F(k - k_F) \pm |\alpha_R k_F - \gamma h_y|$$

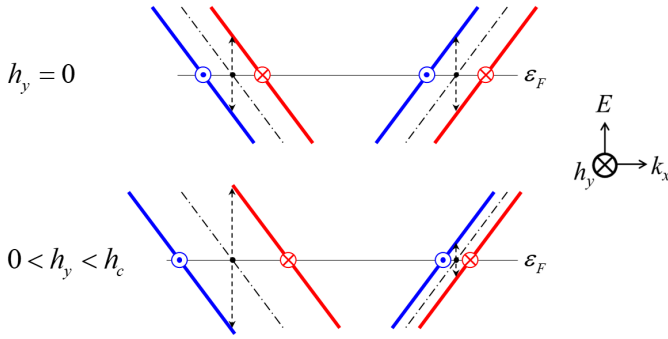


FIG. 2. The magnetic field dependence of the Fermi points in one-dimension. The circles with blue dot and red cross indicate spin direction parallel and anti-parallel to the y -direction on each Fermi point, respectively. The horizontal thin line denotes the Fermi energy $\varepsilon_F = v_F k_F$. The upper panel shows the dispersion relation without an in-plane magnetic field h_y , which is perpendicular to a x -direction, and the lower one is for the case of $0 < h_y < h_c$, where $h_c \equiv \alpha_R k_F / \gamma$.

(SC_R) and M is given by,

$$\begin{aligned} H_{TL} &= \sum_{k,q,\sigma=\pm} t \left[(a_{L,k\sigma}^\dagger + b_{L,k\sigma}^\dagger)(a_{q\sigma} + b_{q\sigma}) + H.c. \right] \\ &\quad - \sum_{k,q,\sigma=\pm} t \left[(a_{L,-k\sigma} + b_{L,-k\sigma})(a_{-q\sigma}^\dagger + b_{-q\sigma}^\dagger) + H.c. \right], \\ H_{TR} &= \sum_{k,q,\sigma=\pm} t e^{i(k-q)d} \left[(a_{R,k\sigma}^\dagger + b_{R,k\sigma}^\dagger)(a_{q\sigma} + b_{q\sigma}) + H.c. \right] \\ &\quad - \sum_{k,q,\sigma=\pm} t e^{i(k-q)d} \left[(a_{R,-k\sigma} + b_{R,-k\sigma})(a_{-q\sigma}^\dagger + b_{-q\sigma}^\dagger) \right. \\ &\quad \left. + H.c. \right], \end{aligned} \quad (10)$$

$$\quad (11)$$

where the electrode distance between SC_L and SC_R is denoted by d . The tunneling matrix element t is assumed to be constant.

III. JOSEPHSON COUPLING ENERGY BETWEEN TWO SUPERCONDUCTORS

The Josephson coupling energy F is proportional to $\cos(\phi + \phi_0)$ with a phase difference of SCs ϕ and a constant ϕ_0 . I_c is estimated by the amplitude of the $\cos \phi$ term. In the fourth order of t (See Fig. 3), F is given by,

$$F = \frac{t^4}{4} (\pi \rho_F)^2 \sum_n \frac{|\Delta|^2}{\omega_n^2 + |\Delta|^2} \left[e^{+i\phi} \sum_{k,k'} \mathcal{A}(k, k') e^{+i(k-k')d} + e^{-i\phi} \sum_{k,k'} \mathcal{A}(k, k') e^{-i(k-k')d} \right], \quad (12)$$

$$\mathcal{A}(k, k') \equiv \sum_{\substack{m=1,2 \\ m'=3,4}} \left\{ g_{m++}(\mathbf{k}') g_{m'--}^*(-\mathbf{k}) + g_{m--}(\mathbf{k}') g_{m'+++}^*(-\mathbf{k}) - [g_{m-+}(\mathbf{k}') g_{m'-+}^*(-\mathbf{k}) + g_{m+-}(\mathbf{k}') g_{m'+-}^*(-\mathbf{k})] \right\}. \quad (13)$$

with $\mathbf{k} \equiv (k, i\omega_n)$ and Matsubara frequency of fermion ω_n . The prime indicates a different momentum and a different frequency. The Greens functions $g_{n\alpha\beta}$ ($n = 1 \sim$

4 and $\alpha, \beta = +, -$) is given by,

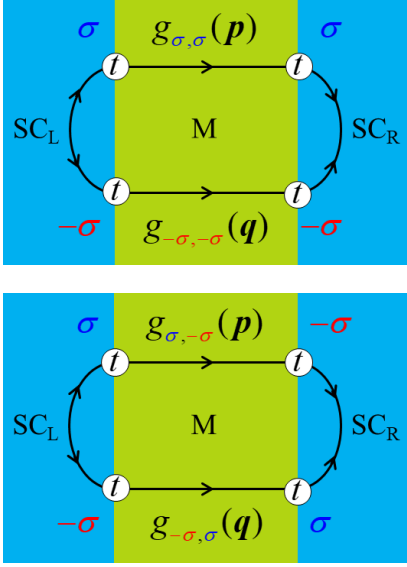


FIG. 3. Diagrams contributing to the Josephson coupling. The Josephson diode effect comes from the process of the lower panel

$$\begin{pmatrix} g_{1++}(\mathbf{k}) & g_{1+-}(\mathbf{k}) \\ g_{1-+}(\mathbf{k}) & g_{1--}(\mathbf{k}) \end{pmatrix} = \frac{1}{(vp + \Lambda_- - i\omega_n)(vp - \Lambda_- - i\omega_n)} \begin{pmatrix} i\omega_n - vp - \gamma h_z & +i\lambda_- \\ -i\lambda_- & i\omega_n - vp + \gamma h_z \end{pmatrix}, \quad (14)$$

$$\begin{pmatrix} g_{2++}(\mathbf{k}) & g_{2+-}(\mathbf{k}) \\ g_{2-+}(\mathbf{k}) & g_{2--}(\mathbf{k}) \end{pmatrix} = \frac{1}{(vq + \Lambda_+ + i\omega_n)(vq - \Lambda_+ + i\omega_n)} \begin{pmatrix} i\omega_n + vq - \gamma h_z & -i\lambda_+ \\ +i\lambda_+ & i\omega_n + vq + \gamma h_z \end{pmatrix}, \quad (15)$$

$$\begin{pmatrix} g_{3++}^*(-\mathbf{k}) & g_{3+-}^*(-\mathbf{k}) \\ g_{3-+}^*(-\mathbf{k}) & g_{3--}^*(-\mathbf{k}) \end{pmatrix} = \frac{1}{(vq + \Lambda_- - i\omega_n)(vq - \Lambda_- - i\omega_n)} \begin{pmatrix} i\omega_n - vq + \gamma h_z & -i\lambda_- \\ +i\lambda_- & i\omega_n - vq - \gamma h_z \end{pmatrix}, \quad (16)$$

$$\begin{pmatrix} g_{4++}^*(-\mathbf{k}) & g_{4+-}^*(-\mathbf{k}) \\ g_{4-+}^*(-\mathbf{k}) & g_{4--}^*(-\mathbf{k}) \end{pmatrix} = \frac{1}{(vp + \Lambda_+ + i\omega_n)(vp - \Lambda_+ + i\omega_n)} \begin{pmatrix} i\omega_n + vp + \gamma h_z & i\lambda_+ \\ -i\lambda_+ & i\omega_n + vp - \gamma h_z \end{pmatrix}, \quad (17)$$

$$\lambda_- \equiv (\alpha_R k_F - \gamma h_y), \quad (18)$$

$$\lambda_+ \equiv (\alpha_R k_F + \gamma h_y). \quad (19)$$

$$vp \equiv v_F(k - k_F), \quad (20)$$

$$vq \equiv v_F(k + k_F). \quad (21)$$

by which I_c is estimated as $t^4 \mathcal{U} \mathcal{V}$. One of prefactors \mathcal{U} is given by,

$$\begin{aligned} \mathcal{U} &= \left(\frac{2\pi}{v_F}\right)^2 T \sum_n \frac{(\pi\rho_F)^2 \Delta^2}{\omega_n^2 + \Delta^2} e^{-2|\omega_n|d/v_F} \theta(-\omega_n), \quad (23) \\ &= \left(\frac{2\pi}{v_F}\right)^2 \frac{(\pi\rho_F)^2}{2\Delta^2} \int_0^\infty dx \sin x \left[\operatorname{cosech} \left(\frac{\pi T x}{\Delta} + \frac{d}{\xi_T} \right) \right], \quad (24) \end{aligned}$$

Summing over k and k' , Eq. (12) is reduced to,

$$F = -t^4 \mathcal{U} \mathcal{V} \cos \phi, \quad (22)$$

$$\propto \begin{cases} \exp\left(-\frac{d}{\xi_T}\right) & \text{for } d/\xi_T \gg 1 \\ \frac{\xi_0}{d} & \text{for } T \rightarrow 0 \end{cases}, \quad (25)$$

with $\xi_T \equiv v_F/2\pi T$ and $\xi_0 \equiv v_F/2\Delta$. Details to derive Eqs. (24) and (25) are given in Ref. [44]. The \mathcal{U} ex-

ponentially decays with d for $d/\xi_T \gg 1$ and becomes a power-low decay at low temperatures. The other factor

\mathcal{V} , on the other hand, includes the spin-orbit interaction and is given by,

$$\mathcal{V} = \left[\cos\left(\frac{\Lambda_- d}{v_F}\right) \cos\left(\frac{\Lambda_+ d}{v_F}\right) - \frac{(\gamma h_z)^2}{\Lambda_- \Lambda_+} \sin\left(\frac{\Lambda_- d}{v_F}\right) \sin\left(\frac{\Lambda_+ d}{v_F}\right) \right] + \frac{\lambda_- \lambda_+}{\Lambda_- \Lambda_+} \sin\left(\frac{\Lambda_- d}{v_F}\right) \sin\left(\frac{\Lambda_+ d}{v_F}\right), \quad (26)$$

$$\Lambda_{\pm} \equiv \sqrt{(\gamma h_z)^2 + (\alpha_R k_F \pm \gamma h_y)^2}. \quad (27)$$

This factor Eq. (26) essentially changes the transport property of the Josephson junction, because \mathcal{V} can be negative, i.e., the π -junction [23, 24]. In Eq. (26), the first and second terms are the contribution of diagonal part, i.e., $g_{n++}g_{m--}^* + g_{n--}g_{m++}^*$, and the last term is the result of the off-diagonal part, i.e., $g_{n+-}g_{m-+}^* + g_{n-+}g_{m+-}^*$, respectively.

For $h_z = 0$, $h_y = 0$, and $\alpha_R \neq 0$, Eq. (26) becomes constant as,

$$\mathcal{V} = 1. \quad (28)$$

The spin-orbit interaction does not change the coupling between singlet SCs. For $h_z \neq 0$, $h_y = 0$, and $\alpha_R = 0$, Eq. (26) leads to,

$$\mathcal{V} = \cos\left(\frac{2\gamma h_z d}{v_F}\right), \quad (29)$$

which reproduces the case of the SC/ferromagnet/SC (SFS) junction [23–34, 44]. This is also the case for $h_z = 0$, $h_y \neq 0$, and $\alpha_R \neq 0$,

$$\mathcal{V} = \begin{cases} \cos\left[\frac{(\Lambda_+ - \Lambda_-) d}{v_F}\right] & \text{for } \lambda_- > 0 \\ \cos\left[\frac{(\Lambda_+ + \Lambda_-) d}{v_F}\right] & \text{for } \lambda_- < 0 \end{cases} \quad (30)$$

$$= \cos\left(\frac{2\gamma h_y d}{v_F}\right), \quad (31)$$

which is equivalent to Eq. (29) except for the direction of external magnetic field. This is consistent with the previous study by Bezuglyi et al. [22]. The spin-orbit interaction does not appear in the coupling energy in both cases of h_z and h_y . The coupling between singlet SCs is not affected by the spin-orbit interaction in a uniform magnetic field, unless spatial magnetic structure is involved [45–48]. Notably, Eq. (30) has two regions resulting from the topological change of the spin configuration at the Fermi energy (Fig. 2). It is

that $\lambda_- = 0$ corresponds to $h_y = h_c$. In spite of the topological change of the spin configuration, the results are identical as Eq. (31) without any singularity.

IV. JOSEPHSON DIODE EFFECT DEPENDING ON ELECTRODE DISTANCE

The amplitude of current flowing from one SC to the other through the Rashba system must be identical in each region because of the continuity of electronic current. As a result, the electronic state in the Rashba system is changed to a non-equilibrium steady state. Such a state can be described by the Fermi momentum shift q_{ex} as, $+k_F \rightarrow +k_F + q_{ex}/2$ and $-k_F \rightarrow -k_F + q_{ex}/2$ in the one dimensional model. The current I_B is generally described by $I_B = |e|v_d n_e S$ with drift velocity v_d , electron density n_e , and cross section S . It should be noted that v_d is different from v_F , e.g., $v_d \sim 10^{-3}$ m/s [49]. To bring I_B into the one-dimensional model, we define a current density per channel by $i_B \equiv I_B/S$ Ampere(A)/channel with S in a unit of \AA^2 . Here we discuss the relation between q_{ex} and i_B in our one-dimensional model. The electron density contributing to the current is given by $n_e = |q_{ex}|/(2\pi)$, which is a difference of Fermi volume with and without i_B . Therefore, I_B is related with q_{ex} by $i_B = -|e|v_d q_{ex}/(2\pi)$. In the experiment, e.g., Ref. [15], I_B is of the order of 0.1 mA and the cross sectional area $S = 10 \text{ nm} \times 50 \text{ }\mu\text{m} = 0.5 \times 10^8 \text{ }\text{\AA}^2$. Therefore, we can estimate as $q_{ex} = -2\pi i_B/(|e|v_d) \sim 4 \text{ \AA}^{-1}$. The Fermi momentum k_F of a metal is typically $\sim 1 \text{ \AA}^{-1}$ [50]. On the discussion above, the magnitude of q_{ex} is estimated to be comparable or a little larger than k_F .

The current-voltage curve of the Josephson junction is obtained by biasing the junction with current and measuring the voltage. Under the current bias, λ_- and λ_+ in Eqs.(18) and (19) are substituted by,

$$\lambda'_- = \alpha_R (k_F + q_{ex}/2) - \gamma h_y, \quad (32)$$

$$\lambda'_+ = \alpha_R (k_F - q_{ex}/2) + \gamma h_y. \quad (33)$$

The coupling energy under the current bias F_{bias} in the fourth order of t is given by,

$$F_{bias} = -t^4 \mathcal{U} \mathcal{V}_{bias} \cos(\phi + q_{ex}d), \quad (34)$$

$$\begin{aligned} \mathcal{V}_{bias} &= \mathcal{V} + \frac{q_{ex}}{k_F} \frac{\alpha_R k_F \gamma h_y}{\Lambda_- \Lambda_+} \sin\left(\frac{\Lambda'_- d}{\hbar v_F}\right) \sin\left(\frac{\Lambda'_+ d}{\hbar v_F}\right) - \frac{\alpha_R^2 q_{ex}^2}{4\Lambda_- \Lambda_+} \sin\left(\frac{\Lambda_- d}{\hbar v_F}\right) \sin\left(\frac{\Lambda_+ d}{\hbar v_F}\right), \\ &\equiv \mathcal{V} + \delta\mathcal{V}_o - \delta\mathcal{V}_e, \end{aligned} \quad (35)$$

where \hbar is explicitly written to discuss a length scale below. It should be noted that the amplitude of the cosine term in Eq. (34) is modified by the q_{ex} , i.e., i_B . The second term of Eq. (35), $\delta\mathcal{V}_o$, represents the Josephson diode effect,

$$I_c^+ - I_c^- = 2 \delta\mathcal{V}_o \propto \alpha_R \cdot i_B \cdot h_y, \quad (36)$$

where $q_{ex} = -2\pi i_B / |e| v_d$ is used. The Josephson diode effect requires three factors, i.e., α_R , i_B , and h_y . Since the term is proportional to their product $\alpha_R \cdot i_B \cdot h_y$, the change of I_c , i.e., $I_c^+ - I_c^-$, due to the applied current is odd with respect to a direction of the current or an external magnetic field as is observed in the experiments. More importantly, the Josephson diode effect depends on d as well as i_B and h_y due to the term, $\sin(\Lambda_- d / \hbar v_F) \sin(\Lambda_+ d / \hbar v_F)$, in Eq. (35). The d -dependence of the Josephson diode effect is the important finding of this study and has not been mentioned so far.

The length scale of the Josephson diode effect is determined by Λ_{\pm} composed of $\alpha_R k_F$, γh_y , and γh_z . The $\alpha_R k_F$ corresponds to the band splitting at the Fermi surface and its magnitude ranges from sub meV to several hundreds meV depending on materials and their form, e.g., bulk, film or surface [51–53]. The magnitude of γh_z and γh_y is usually up to 10 T that corresponds to about 1 meV. Using a typical value of $v_F \sim 10^6$ m/s [50] and d in units of nm, the length scale is determined by $d / \hbar v_F \sim 1.52d$ eV $^{-1}$. Below, we consider the case of $h_y = 10$ T and $h_z = 0$ T.

The efficiency of the Josephson diode effect, Q , is defined by $Q \equiv (I_c^+ - I_c^-) / (I_c^+ + I_c^-)$. In our theory, it gives,

$$Q = \frac{\delta\mathcal{V}_o}{\mathcal{V} + \delta\mathcal{V}_e}, \quad (37)$$

$$\sim \frac{q_{ex}}{k_F} \frac{\gamma h_y}{\alpha_R k_F} \frac{1}{2} \left[1 - \frac{\cos(2\gamma h_y d / \hbar v_F)}{\cos(2\alpha_R k_F d / \hbar v_F)} \right], \quad (38)$$

where terms in the order of $(\gamma h_y / \alpha_R k_F)^2$ are not shown. In Fig. 4, Q is plotted in units of q_{ex} / k_F for (a) $\alpha_R k_F = 5$ meV (green), 10 meV (blue), and 20 meV (red); (b) $\alpha_R k_F = 20$ meV (red), 50 meV (light green), and 100 meV (black). The rectangular area in (a) denoted by the broken line corresponds to the plot area of (b). The red lines in (a) and (b) are identical except for the plot area. The magnitude of Q oscillates with d and changes its sign. It means that the Josephson diode effect can be optimized by tuning of d . This provides a guiding principle for

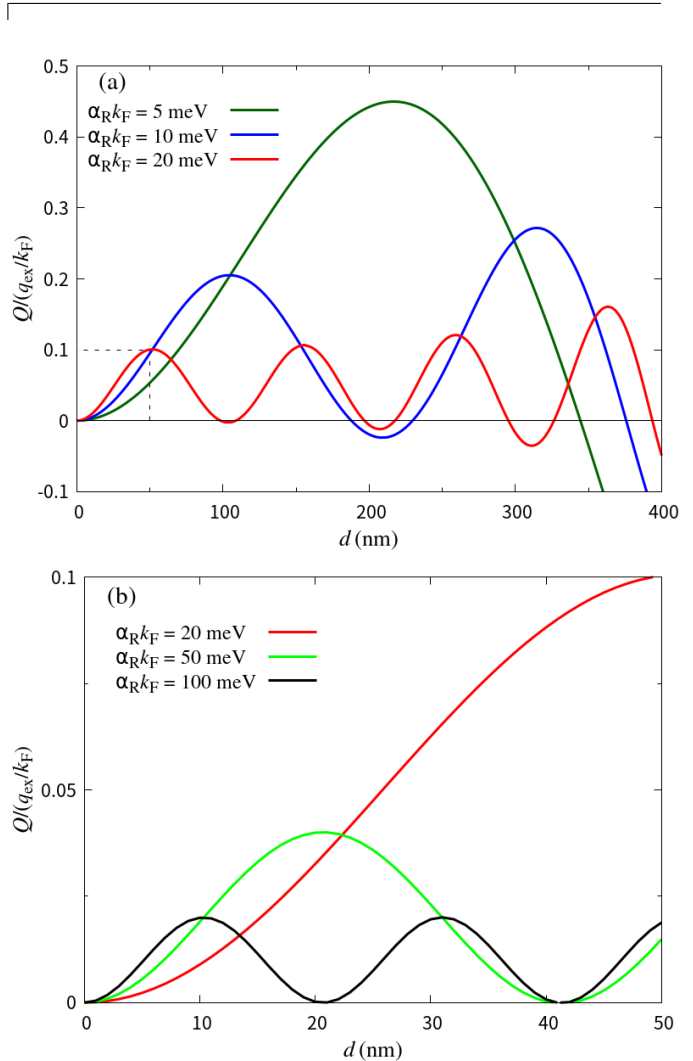


FIG. 4. The d -dependence of Q in units of q_{ex}/k_F with $h_y = 10$ T and $h_z = 0$ T is plotted for (a) $\alpha_R k_F = 5$ meV (green), 10 meV (blue), and 20 meV (red); (b) $\alpha_R k_F = 20$ meV (red), 50 meV (light green), and 100 meV (black). The rectangular area in (a) denoted by the broken line corresponds to the plot area of (b). The red lines in (a) and (b) are the same line except for the plot area.

the Josephson diode device, because d can be controlled in experiments. It is also important that the Josephson diode effect changes its sign with d , even when α_R , q_{ex} and h_y are fixed. To determine not only the magnitude of the Josephson diode effect, but also its sign, we must take care of d as well.

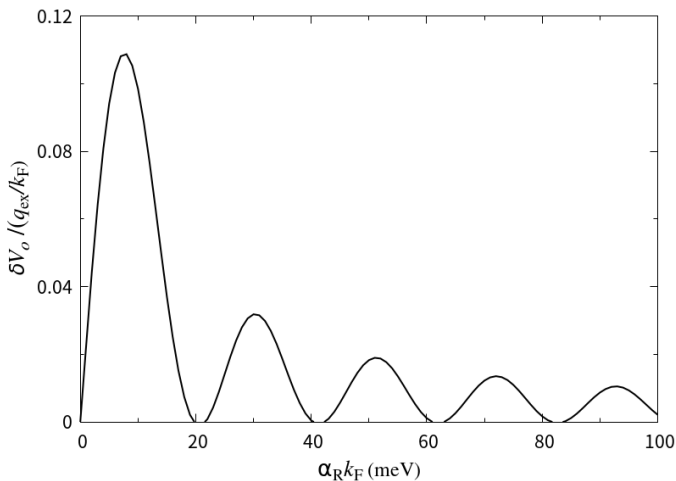


FIG. 5. The $\alpha_R k_F$ -dependence of δV_o with $d = 100$ nm, and $h_y = 10$ T, $h_z = 0$ T.

Increasing $\alpha_R k_F$, the period of the oscillation becomes short and the magnitude is suppressed. This can be understood by Eq. (35),

$$\delta \mathcal{V}_o \sim \frac{1}{2} \frac{q_{ex}}{k_F} \frac{\gamma h_y}{\alpha_R k_F} \left[\cos \left(\frac{2\gamma h_y d}{\hbar v_F} \right) - \cos \left(\frac{2\alpha_R k_F d}{\hbar v_F} \right) \right]. \quad (39)$$

for $\alpha_R k_F \gg h_y$ and $h_z = 0$. In Fig. 4, since $\gamma h_y = 1$ meV is used, the second term of Eq. (39) dominates the d -dependence of Q and the first term is almost 1 in the area of Fig. 4. Equation (39) is a decreasing function with respect to $\alpha_R k_F$. Therefore, the Josephson diode effect becomes smaller for larger values of $\alpha_R k_F$ as shown in Fig. 5. Although the spin-orbit interaction is necessary for the Josephson diode effect, larger α_R does not always results in a larger effect. Sometimes the effect may accidentally disappear, e.g., $\alpha_R k_F \sim 20$ meV in Fig. 5. In general, it is not easy to tune $\alpha_R k_F$, whereas d can be controlled in experiment. Our results suggests that the Josephson diode effect can be optimized by tuning of d .

V. SUMMARY

We theoretically studied the Josephson diode effect in the Josephson junction with singlet superconductors separated by the Rashba system. The coupling energy of superconductors was calculated using the tunneling Hamiltonian with the one-dimensional model. By applying a magnetic field perpendicular to the bias current, there appeared the additional term in the coupling energy explaining the Josephson diode effect. This term is proportional to the bias current and the external magnetic field. Most importantly, the Josephson diode effect depends on

the distance between superconducting electrodes d . In general, it is difficult to tune the band splitting by the spin-orbit interaction, whereas d is experimentally controllable. Our findings suggest that the Josephson diode effect can be optimized by tuning of d . It will help to observe the Josephson diode effect experimentally. The magnitude of the Josephson diode effect is inversely proportional to the band split at the Fermi surface caused by the spin-orbit interaction. Although the spin-orbit interaction is necessary, larger α_R does not always results in a larger effect. Our theory develops a new guiding principle to design the Josephson diode device.

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Appendix A: Current-phase relation

The Josephson coupling energy under a current bias has not been formulated by the tunneling Hamiltonian. It is noted that q_{ex} in Eq. (34) is a function of i_B as discussed in Sec. IV, i.e., $q_{ex} = -2\pi i_B / |e|v_d$. Taking the derivative with respect to ϕ over the sum of Eq. (34) and the external force $i_B \cdot \phi$, we obtain the equation,

$$i_B = t^A \mathcal{U} \mathcal{V}_{bias} \sin \left(\phi - \frac{2\pi d}{|e|v_d} i_B \right). \quad (A1)$$

Solving Eq. (A1) with respect to i_B , the current-phase relation under the current bias is obtained as shown in Fig. 6, in which Eq. (A1) is parameterized by $x \equiv \phi$, $y \equiv i_B$, and $a \equiv 2\pi d / |e|v_d$ and is reduced to $y = \sin(x - a \cdot y)$ with $t^A \mathcal{U} \mathcal{V}_{bias} = 1$. The current-phase relation is modified as that of metallic interface by increasing a . When the parameter a is much larger than 1, the current-phase relation deviates from the sinusoidal behavior. Since we adopted the one-dimensional model for the two-dimensional system, we cannot exactly assign the value of a . For studying the Josephson diode effect, we assumed that the current phase relation is a periodic function like that in Fig. 6. Although the exact formula of the current-phase relation under the current bias is not the main purpose of this study, it is also interesting and will be numerically studied using the two-dimensional system elsewhere in future.

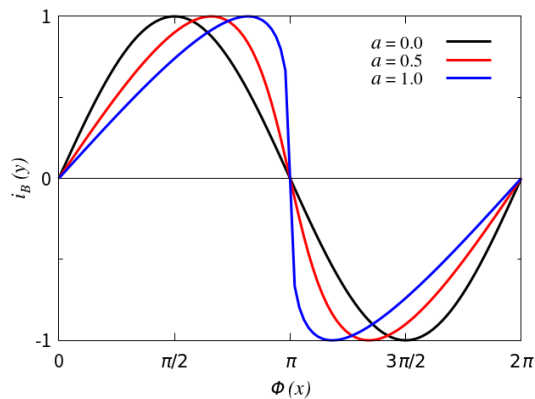


FIG. 6. The current-phase relation obtained by solving $y = \sin(x - a \cdot y)$ which is reduced from Eq. (A1) with $y \equiv i_B$, $x \equiv \phi$, $a \equiv 2\pi d/|e|v_d$, and $t^4 \mathcal{U} \mathcal{V}_{bias} = 1$.

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